

**Vorläufige Daten
preliminary data**

IGBT-Wechselrichter / IGBT-inverter

Höchstzulässige Werte / maximum rated values

| | | | | |
|--|--|-----------------------------|----------|--------|
| Kollektor-Emitter-Sperrspannung collector-emitter voltage | $T_{vj} = 25^{\circ}\text{C}$ | V_{CES} | 600 | V |
| Kollektor-Dauergleichstrom DC-collector current | $T_C = 70^{\circ}\text{C}$ $T_C = 25^{\circ}\text{C}$ | $I_{C\text{ nom}}$ I_C | 75 95 | A A |
| Periodischer Kollektor Spitzenstrom repetitive peak collector current | $t_p = 1\text{ ms}, T_C = 70^{\circ}\text{C}$ | I_{CRM} | 150 | A |
| Gesamt-Verlustleistung total power dissipation | $T_C = 25^{\circ}\text{C}$ | P_{tot} | 340 | W |
| Gate-Emitter-Spitzenspannung gate-emitter peak voltage | | V_{GES} | +/-20 | V |

Charakteristische Werte / characteristic values

| | | | min. | typ. | max. | |
|--|---|---------------------|------|----------------|------|--------------------------------|
| Kollektor-Emitter Sättigungsspannung collector-emitter saturation voltage | $I_C = 75\text{ A}, V_{GE} = 15\text{ V}, T_{vj} = 25^{\circ}\text{C}$ $I_C = 75\text{ A}, V_{GE} = 15\text{ V}, T_{vj} = 125^{\circ}\text{C}$ | $V_{CE\text{ sat}}$ | | 1,95 2,20 | 2,55 | V V |
| Gate-Schwellenspannung gate threshold voltage | $I_C = 1,50\text{ mA}, V_{CE} = V_{GE}, T_{vj} = 25^{\circ}\text{C}$ | V_{GEth} | 4,5 | 5,5 | 6,5 | V |
| Gateladung gate charge | $V_{GE} = -15\text{ V} \dots +15\text{ V}$ | Q_G | | 0,40 | | μC |
| Interner Gatewiderstand internal gate resistor | $T_{vj} = 25^{\circ}\text{C}$ | R_{Gint} | | 0,0 | | Ω |
| Eingangskapazität input capacitance | $f = 1\text{ MHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$ | C_{ies} | | 3,30 | | nF |
| Rückwirkungskapazität reverse transfer capacitance | $f = 1\text{ MHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$ | C_{res} | | 0,30 | | nF |
| Kollektor-Emitter Reststrom collector-emitter cut-off current | $V_{CE} = 600\text{ V}, V_{GE} = 0\text{ V}, T_{vj} = 25^{\circ}\text{C}$ | I_{CES} | | | 5,0 | mA |
| Gate-Emitter Reststrom gate-emitter leakage current | $V_{CE} = 0\text{ V}, V_{GE} = 20\text{ V}, T_{vj} = 25^{\circ}\text{C}$ | I_{GES} | | | 400 | nA |
| Einschaltverzögerungszeit (ind. Last) turn-on delay time (inductive load) | $I_C = 75\text{ A}, V_{CE} = 300\text{ V}$ $V_{GE} = \pm 15\text{ V}, R_{Gon} = 3,0\ \Omega, T_{vj} = 25^{\circ}\text{C}$ $V_{GE} = \pm 15\text{ V}, R_{Gon} = 3,0\ \Omega, T_{vj} = 125^{\circ}\text{C}$ | $t_{d\text{ on}}$ | | 0,045 0,05 | | μs μs |
| Anstiegszeit (induktive Last) rise time (inductive load) | $I_C = 75\text{ A}, V_{CE} = 300\text{ V}$ $V_{GE} = \pm 15\text{ V}, R_{Gon} = 3,0\ \Omega, T_{vj} = 25^{\circ}\text{C}$ $V_{GE} = \pm 15\text{ V}, R_{Gon} = 3,0\ \Omega, T_{vj} = 125^{\circ}\text{C}$ | t_r | | 0,013 0,015 | | μs μs |
| Abschaltverzögerungszeit (ind. Last) turn-off delay time (inductive load) | $I_C = 75\text{ A}, V_{CE} = 300\text{ V}$ $V_{GE} = \pm 15\text{ V}, R_{Goff} = 3,0\ \Omega, T_{vj} = 25^{\circ}\text{C}$ $V_{GE} = \pm 15\text{ V}, R_{Goff} = 3,0\ \Omega, T_{vj} = 125^{\circ}\text{C}$ | $t_{d\text{ off}}$ | | 0,14 0,155 | | μs μs |
| Fallzeit (induktive Last) fall time (inductive load) | $I_C = 75\text{ A}, V_{CE} = 300\text{ V}$ $V_{GE} = \pm 15\text{ V}, R_{Goff} = 3,0\ \Omega, T_{vj} = 25^{\circ}\text{C}$ $V_{GE} = \pm 15\text{ V}, R_{Goff} = 3,0\ \Omega, T_{vj} = 125^{\circ}\text{C}$ | t_f | | 0,02 0,035 | | μs μs |
| Einschaltverlustenergie pro Puls turn-on energy loss per pulse | $I_C = 75\text{ A}, V_{CE} = 300\text{ V}, L_s = 15\text{ nH}$ $V_{GE} = \pm 15\text{ V}, R_{Gon} = 3,0\ \Omega, T_{vj} = 25^{\circ}\text{C}$ $V_{GE} = \pm 15\text{ V}, R_{Gon} = 3,0\ \Omega, T_{vj} = 125^{\circ}\text{C}$ | E_{on} | | 0,50 0,90 | | mJ mJ |
| Abschaltverlustenergie pro Puls turn-off energy loss per pulse | $I_C = 75\text{ A}, V_{CE} = 300\text{ V}, L_s = 15\text{ nH}$ $V_{GE} = \pm 15\text{ V}, R_{Goff} = 3,0\ \Omega, T_{vj} = 25^{\circ}\text{C}$ $V_{GE} = \pm 15\text{ V}, R_{Goff} = 3,0\ \Omega, T_{vj} = 125^{\circ}\text{C}$ | E_{off} | | 1,35 1,95 | | mJ mJ |
| Kurzschlußverhalten SC data | $t_p \leq 10\ \mu\text{s}, V_{GE} \leq 15\text{ V}$ $T_{vj} \leq 125^{\circ}\text{C}, V_{CC} = 360\text{ V}, V_{CEmax} = V_{CES} - L_{sCE} \cdot di/dt$ | I_{SC} | | 340 | | A |
| Innerer Wärmewiderstand thermal resistance, junction to case | pro IGBT per IGBT | R_{thJC} | | | 0,37 | K/W |

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Diode-Wechselrichter / diode-inverter

Höchstzulässige Werte / maximum rated values

| | | | | |
|---|--|-----------|------|------------------|
| Periodische Spitzensperrspannung repetitive peak reverse voltage | $T_{vj} = 25^{\circ}\text{C}$ | V_{RRM} | 600 | V |
| Dauergleichstrom DC forward current | | I_F | 75 | A |
| Periodischer Spitzenstrom repetitive peak forward current | $t_p = 1\text{ ms}$ | I_{FRM} | 150 | A |
| Grenzlastintegral I^2t - value | $V_R = 0\text{ V}, t_p = 10\text{ ms}, T_{vj} = 125^{\circ}\text{C}$ | I^2t | 1200 | A ² s |

Charakteristische Werte / characteristic values

| | | | min. | typ. | max. | |
|---|--|------------|------|--------------|------|--------------------------------|
| Durchlassspannung forward voltage | $I_F = 75\text{ A}, V_{GE} = 0\text{ V}, T_{vj} = 25^{\circ}\text{C}$ $I_F = 75\text{ A}, V_{GE} = 0\text{ V}, T_{vj} = 125^{\circ}\text{C}$ | V_F | | 1,25 1,20 | 1,60 | V V |
| Rückstromspitze peak reverse recovery current | $I_F = 75\text{ A}, -di_F/dt = 4000\text{ A}/\mu\text{s}$ $V_R = 300\text{ V}, V_{GE} = -15\text{ V}, T_{vj} = 25^{\circ}\text{C}$ $V_R = 300\text{ V}, V_{GE} = -15\text{ V}, T_{vj} = 125^{\circ}\text{C}$ | I_{RM} | | 125 135 | | A A |
| Sperrverzögerungsladung recovered charge | $I_F = 75\text{ A}, -di_F/dt = 4000\text{ A}/\mu\text{s}$ $V_R = 300\text{ V}, V_{GE} = -15\text{ V}, T_{vj} = 25^{\circ}\text{C}$ $V_R = 300\text{ V}, V_{GE} = -15\text{ V}, T_{vj} = 125^{\circ}\text{C}$ | Q_r | | 5,10 7,90 | | μC μC |
| Abschaltenergie pro Puls reverse recovery energy | $I_F = 75\text{ A}, -di_F/dt = 4000\text{ A}/\mu\text{s}$ $V_R = 300\text{ V}, V_{GE} = -15\text{ V}, T_{vj} = 25^{\circ}\text{C}$ $V_R = 300\text{ V}, V_{GE} = -15\text{ V}, T_{vj} = 125^{\circ}\text{C}$ | E_{rec} | | 1,65 2,55 | | mJ mJ |
| Innerer Wärmewiderstand thermal resistance, junction to case | pro Diode per diode | R_{thJC} | | | 0,73 | K/W |

NTC-Widerstand / NTC-thermistor

Charakteristische Werte / characteristic values

| | | | min. | typ. | max. | |
|--|--|--------------|------|------|------|------------|
| Nennwiderstand rated resistance | $T_C = 25^{\circ}\text{C}$ | R_{25} | | 5,00 | | k Ω |
| Abweichung von R_{100} deviation of R_{100} | $T_C = 100^{\circ}\text{C}, R_{100} = 493\ \Omega$ | $\Delta R/R$ | -5 | | 5 | % |
| Verlustleistung power dissipation | $T_C = 25^{\circ}\text{C}$ | P_{25} | | | 20,0 | mW |
| B-Wert B-value | $R_2 = R_{25} \exp [B_{25}/50(1/T_2 - 1/(298,15\text{ K}))]$ | $B_{25}/50$ | | 3375 | | K |

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Modul / module

| | | | | | |
|--|--|----------------------|--------------------------------|------|---------|
| Isolations-Prüfspannung insulation test voltage | RMS, f = 50 Hz, t = 1 min. | V _{ISO} | 2,5 | | kV |
| Material Modulgrundplatte material of module baseplate | | | Cu | | |
| Material für innere Isolation material for internal insulation | | | Al ₂ O ₃ | | |
| Kriechstrecke creepage distance | Kontakt - Kühlkörper / terminal to heatsink Kontakt - Kontakt / terminal to terminal | | 10,0 | | mm |
| Luftstrecke clearance distance | Kontakt - Kühlkörper / terminal to heatsink Kontakt - Kontakt / terminal to terminal | | 7,50 | | mm |
| Vergleichszahl der Kriechwegbildung comparative tracking index | | CTI | > 225 | | |
| | | | min. | typ. | max. |
| Übergangs-Wärmewiderstand thermal resistance, case to heatsink | pro Modul / per module $\lambda_{\text{Paste}} = 1 \text{ W}/(\text{m}\cdot\text{K}) / \lambda_{\text{grease}} = 1 \text{ W}/(\text{m}\cdot\text{K})$ | R _{thCH} | | 0,02 | K/W |
| Modulinduktivität stray inductance module | | L _{sCE} | | 19 | nH |
| Modulleitungswiderstand, Anschlüsse - Chip module lead resistance, terminals - chip | T _C = 25°C, pro Schalter / per switch | R _{CC'+EE'} | | 2,50 | mΩ |
| Höchstzulässige Sperrschichttemperatur maximum junction temperature | | T _{vj max} | | | 150 °C |
| Temperatur im Schaltbetrieb temperature under switching conditions | | T _{vj op} | -40 | | 125 °C |
| Lagertemperatur storage temperature | | T _{stg} | -40 | | 125 °C |
| Anzugsdrehmoment f. mech. Befestigung mounting torque | Schraube / screw M5 | M | 3,00 | - | 6,00 Nm |
| Gewicht weight | | G | | 180 | g |

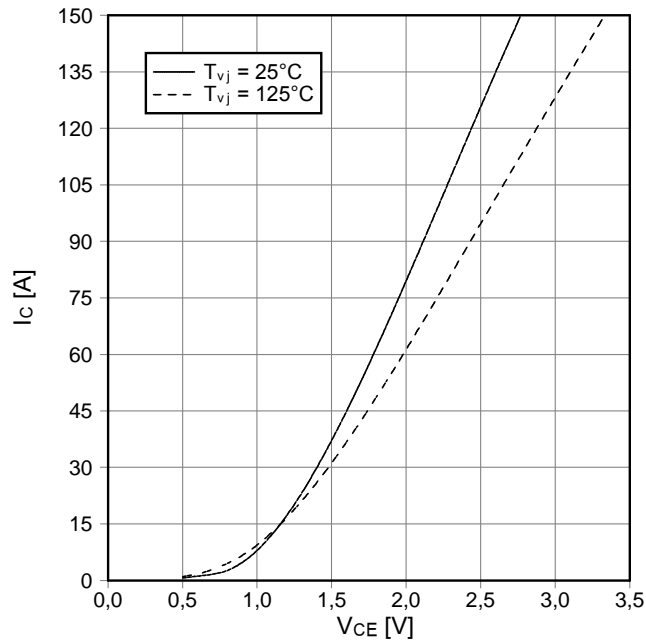
Mit dieser technischen Information werden Halbleiterbauelemente spezifiziert, jedoch keine Eigenschaften zugesichert. Sie gilt in Verbindung mit den zugehörigen technischen Erläuterungen.

This technical information specifies semiconductor devices but guarantees no characteristics. It is valid with the appropriate technical explanations.

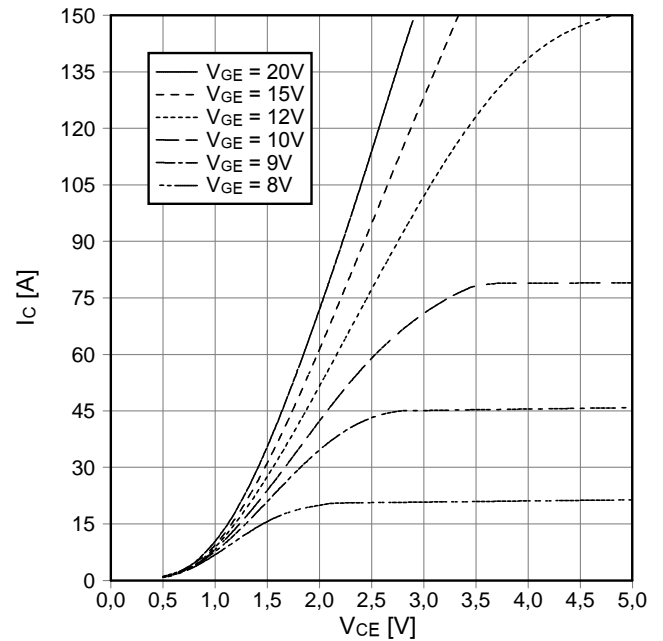
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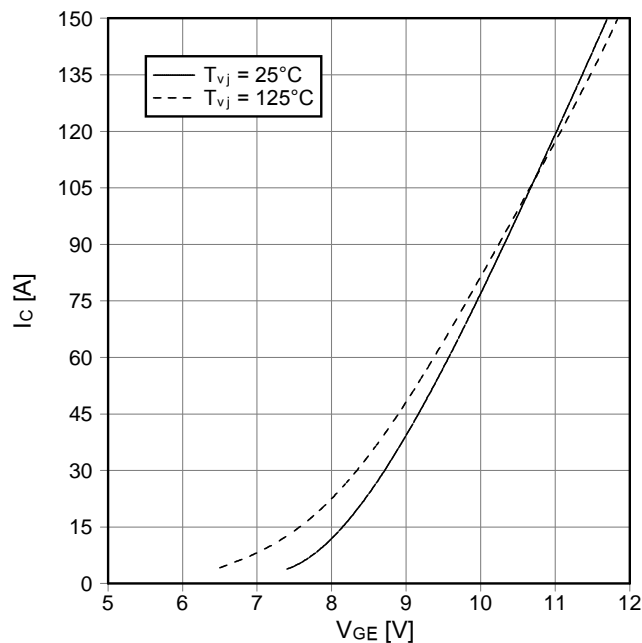
Ausgangskennlinie IGBT-Wechselr. (typisch)
output characteristic IGBT-inverter (typical)
 $I_c = f(V_{CE})$
 $V_{GE} = 15\text{ V}$



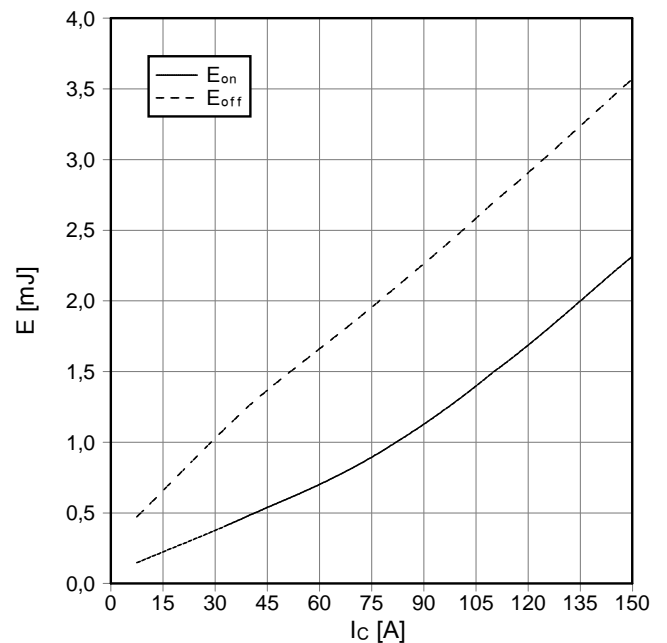
Ausgangskennlinienfeld IGBT-Wechselr. (typisch)
output characteristic IGBT-inverter (typical)
 $I_c = f(V_{CE})$
 $T_{vj} = 125^\circ\text{C}$



Übertragungscharakteristik IGBT-Wechselr. (typisch)
transfer characteristic IGBT-inverter (typical)
 $I_c = f(V_{GE})$
 $V_{CE} = 20\text{ V}$



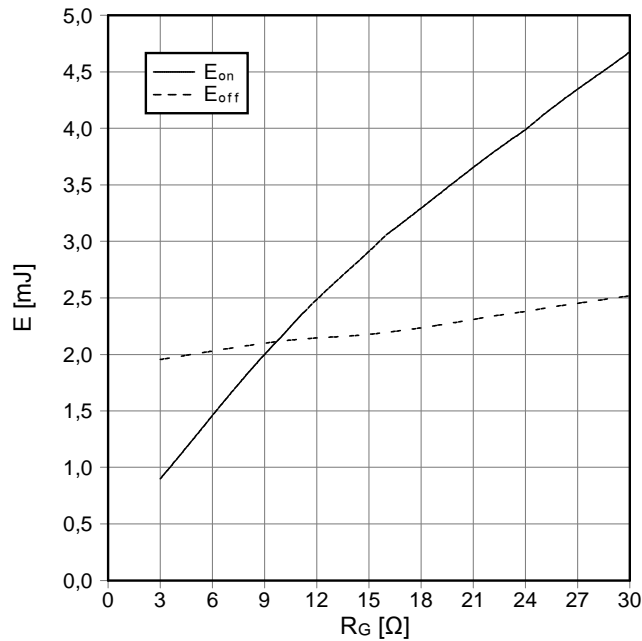
Schaltverluste IGBT-Wechselr. (typisch)
switching losses IGBT-inverter (typical)
 $E_{on} = f(I_c), E_{off} = f(I_c)$
 $V_{GE} = \pm 15\text{ V}, R_{Gon} = 3\ \Omega, R_{Goff} = 3\ \Omega, V_{CE} = 300\text{ V}, T_{vj} = 125^\circ\text{C}$



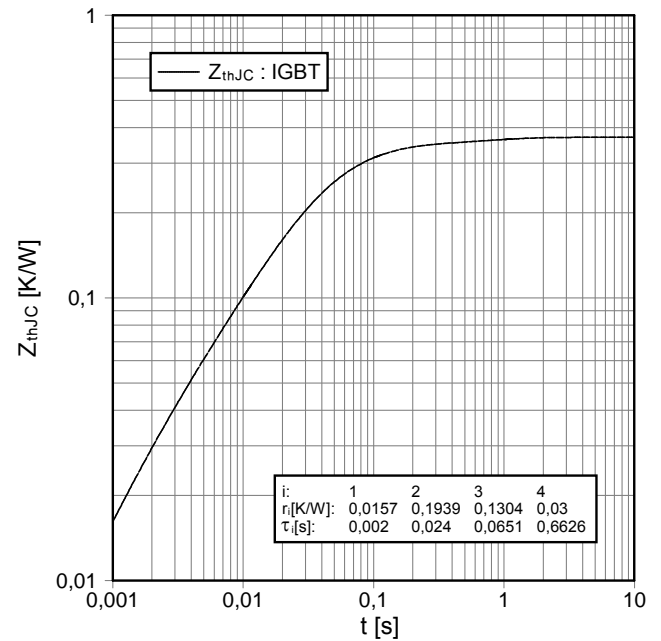
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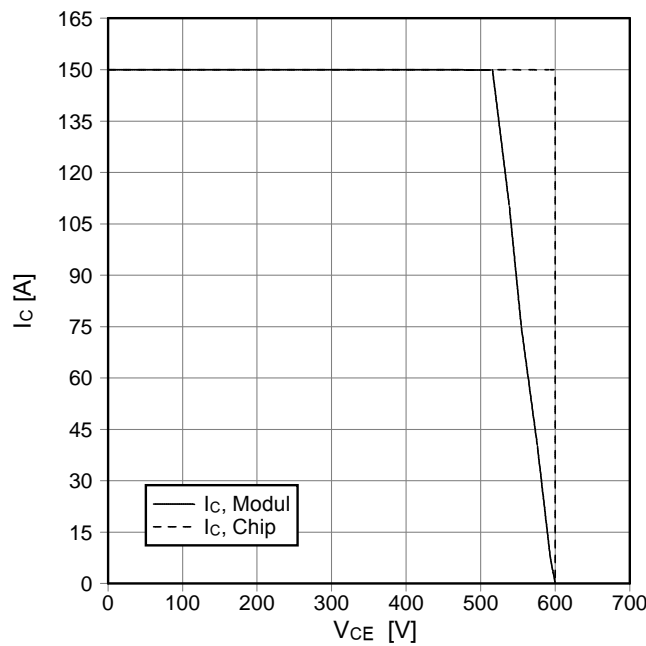
Schaltverluste IGBT-Wechselr. (typisch)
switching losses IGBT-inverter (typical)
 $E_{on} = f(R_G)$, $E_{off} = f(R_G)$
 $V_{GE} = \pm 15\text{ V}$, $I_C = 75\text{ A}$, $V_{CE} = 300\text{ V}$, $T_{vj} = 125^\circ\text{C}$



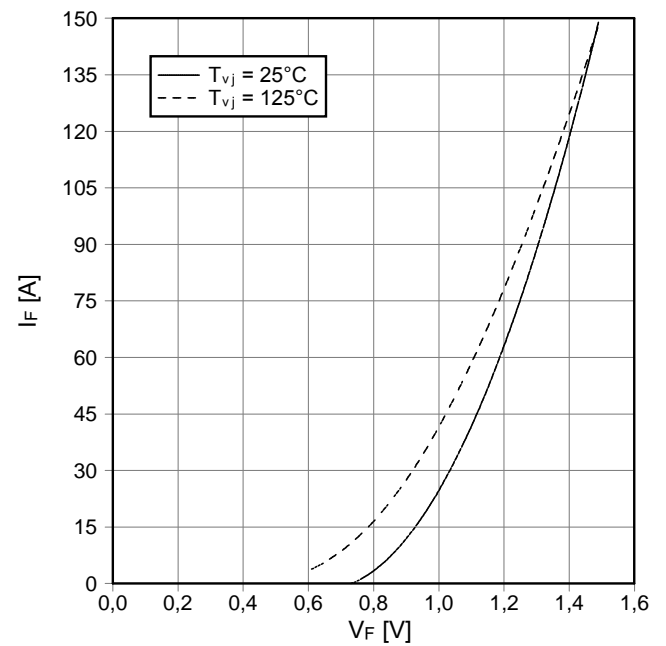
Transienter Wärmewiderstand IGBT-Wechselr.
transient thermal impedance IGBT-inverter
 $Z_{thJC} = f(t)$



Sicherer Rückwärts-Arbeitsbereich IGBT-Wr. (RBSOA)
reverse bias safe operating area IGBT-inv. (RBSOA)
 $I_C = f(V_{CE})$
 $V_{GE} = \pm 15\text{ V}$, $R_{Goff} = 3\ \Omega$, $T_{vj} = 125^\circ\text{C}$



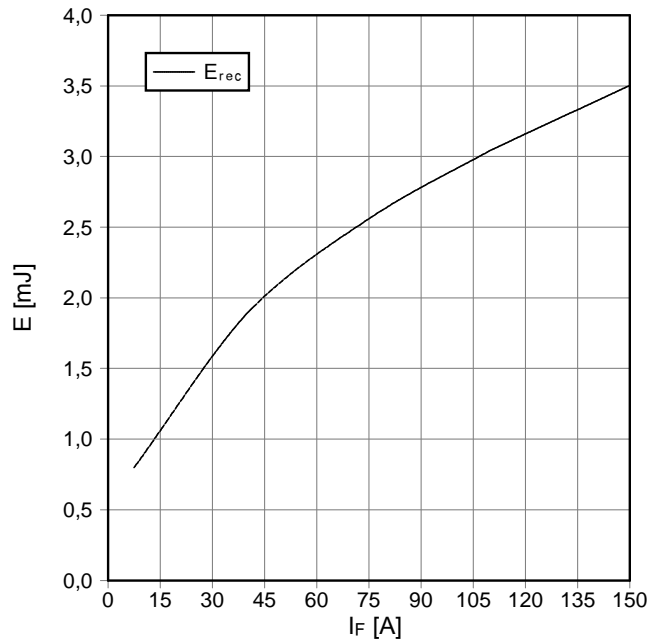
Durchlaßkennlinie der Diode-Wechselr. (typisch)
forward characteristic of diode-inverter (typical)
 $I_F = f(V_F)$



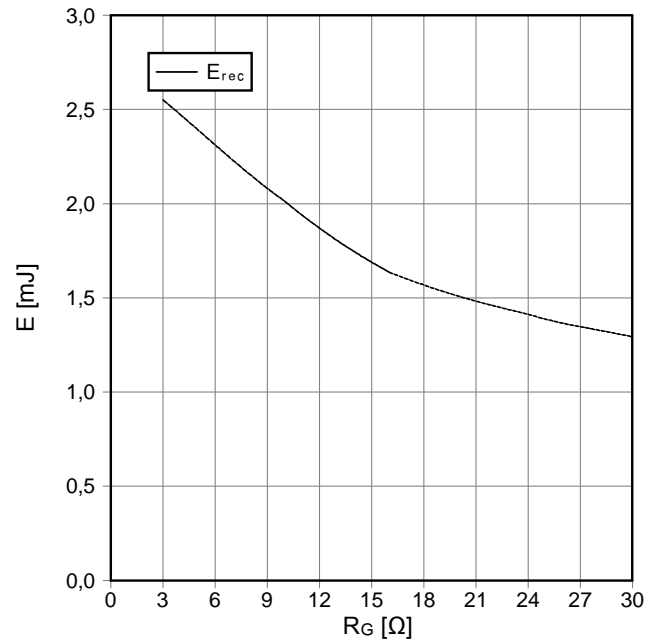
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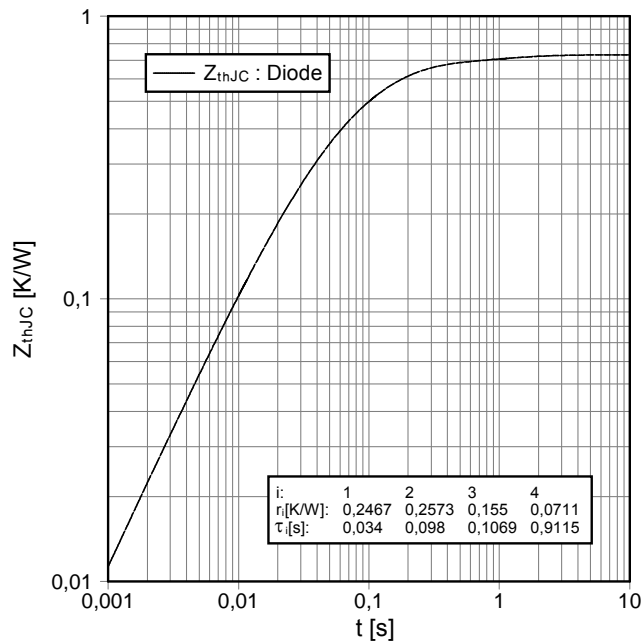
Schaltverluste Diode-Wechselr. (typisch)
switching losses diode-inverter (typical)
 $E_{rec} = f(I_F)$
 $R_{Gon} = 3 \Omega$, $V_{CE} = 300 V$, $T_{vj} = 125^\circ C$



Schaltverluste Diode-Wechselr. (typisch)
switching losses diode-inverter (typical)
 $E_{rec} = f(R_G)$
 $I_F = 75 A$, $V_{CE} = 300 V$, $T_{vj} = 125^\circ C$

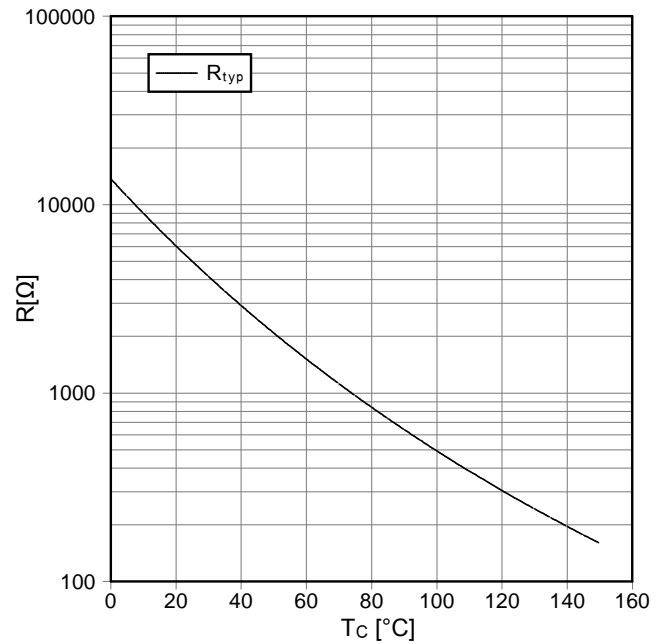


Transienter Wärmewiderstand Diode-Wechselr.
transient thermal impedance diode-inverter
 $Z_{thJC} = f(t)$



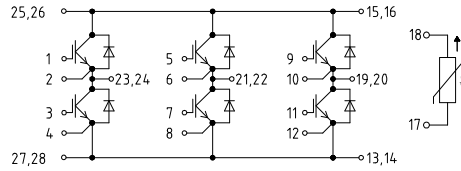
| i: | 1 | 2 | 3 | 4 |
|---------------|--------|--------|--------|--------|
| r_i [K/W]: | 0,2467 | 0,2573 | 0,155 | 0,0711 |
| τ_i [s]: | 0,034 | 0,098 | 0,1069 | 0,9115 |

NTC-Temperaturkennlinie (typisch)
NTC-temperature characteristic (typical)
 $R = f(T)$

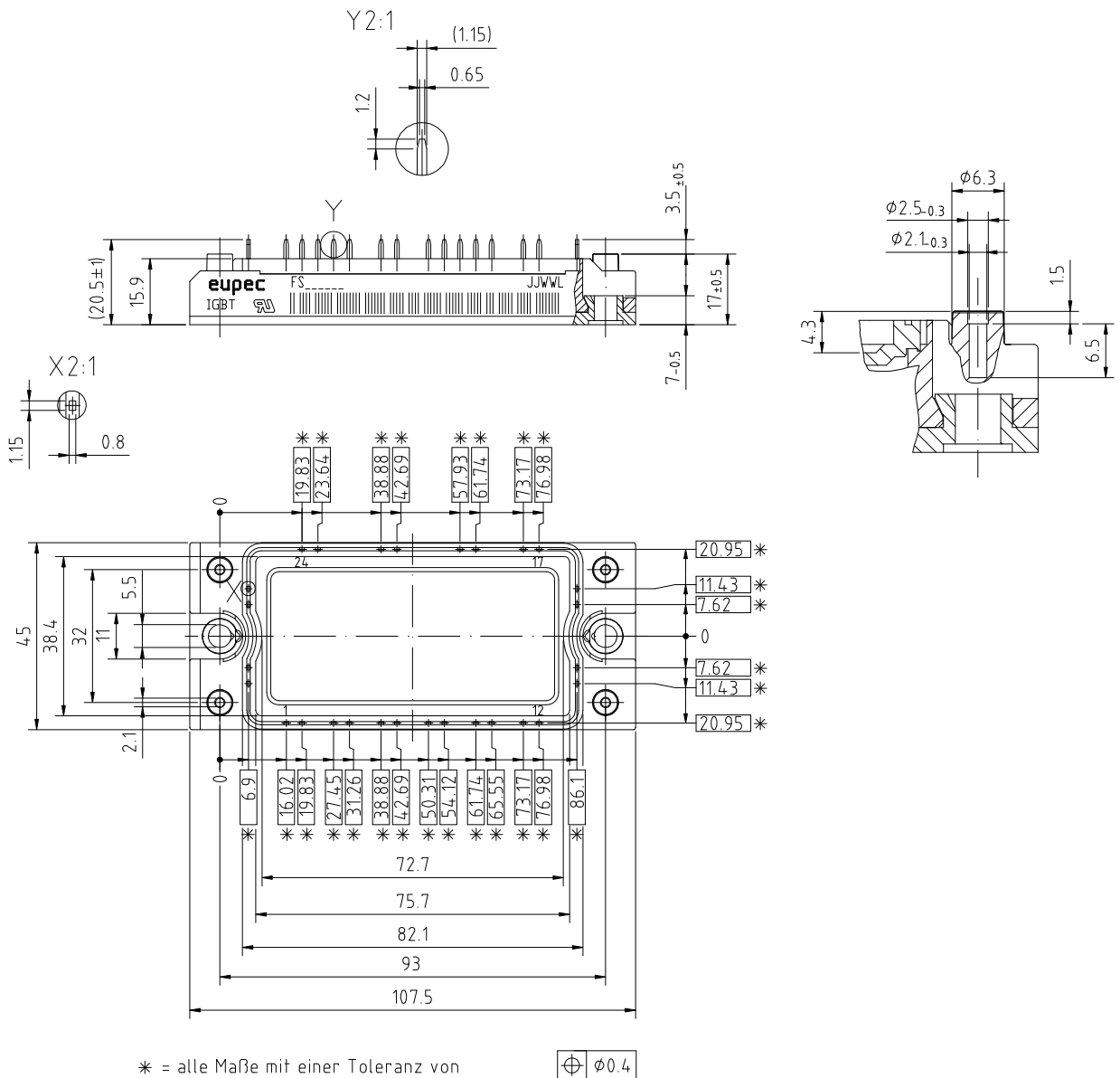


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Schaltplan / circuit diagram



Gehäuseabmessungen / package outlines



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